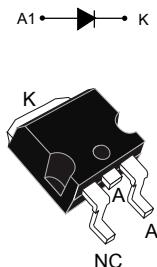


## 1200 V, 15 A, silicon carbide power Schottky diode


**D<sup>2</sup>PAK HV**


Product status link
<a href="#">STPSC15H12G2-TR</a>

Product summary	
I <sub>F(AV)</sub>	15 A
V <sub>RRM</sub>	1200 V
T <sub>j</sub> (max.)	175 °C
V <sub>F</sub> (typ.)	1.35 V

### Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Robust high voltage periphery
- Operating T<sub>j</sub> from -40 °C to 175 °C
- Low V<sub>F</sub>
- D<sup>2</sup>PAK HV creepage distance (anode to cathode) = 5.38 mm min.
- ECOPACK2 compliant

### Applications

- EV Charging station
- DC/DC
- PFC

### Description

This 15 A, 1200 V SiC diode is an ultra-high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 1200 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Housed in D<sup>2</sup>PAK HV, this diode is perfectly suited for a usage in PFC applications, in charging station, DC/DC, easing the compliance to IEC-60664-1.

The [STPSC15H12G2-TR](#) will boost performances in hard switching conditions. Its high forward surge capability ensures good robustness during transient phases.

## 1 Characteristics

**Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified)**

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage ( $T_j = -40^\circ\text{C}$ to $+175^\circ\text{C}$ )	1200	V
$I_{F(RMS)}$	Forward rms current	38	A
$I_{F(AV)}$	Average forward current	15	A
$I_{FRM}$	Repetitive peak forward current	58	A
$I_{FSM}$	Surge non repetitive forward current	105	A
		90	
$T_{stg}$	Storage temperature range	-65 to +175	°C
$T_j$	Operating junction temperature <sup>(1)</sup>	-40 to +175	°C

1.  $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$  condition to avoid thermal runaway for a diode on its own heatsink.

**Table 2. Thermal resistance parameters**

Symbol	Parameter	Value		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Junction to case	0.45	0.6	°C/W

**Table 3. Static electrical characteristics**

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R$ <sup>(1)</sup>	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	-	7.5	90	µA
		$T_j = 150^\circ\text{C}$		-	45	600	
$V_F$ <sup>(2)</sup>	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 15 \text{ A}$	-	1.35	1.50	V
		$T_j = 150^\circ\text{C}$		-	1.75	2.25	

1. Pulse test:  $t_p = 5 \text{ ms}$ ,  $\delta < 2\%$

2. Pulse test:  $t_p = 500 \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

- $P = 1.09 \times I_{F(AV)} + 0.0775 \times I_{F(RMS)}^2$

For more information, please refer to the following application notes related to the power losses:

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

**Table 4. Dynamic electrical characteristics**

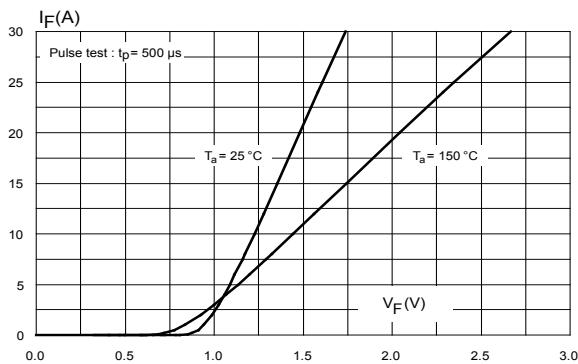
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$Q_{Cj}$ <sup>(1)</sup>	Total capacitive charge	$V_R = 800 \text{ V}$	-	94	-	nC
$C_j$	Total capacitance	$V_R = 0 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	-	1200	-	pF
		$V_R = 800 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	-	78	-	

1.

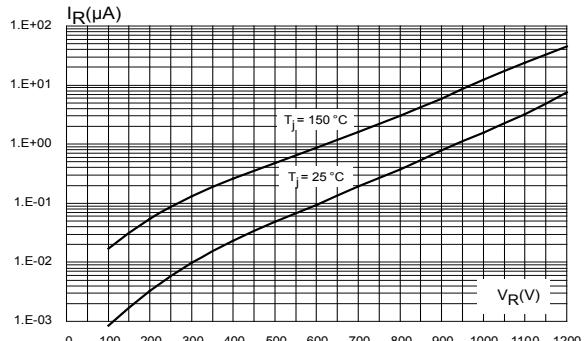
$$\text{Most accurate value for the capacitive charge: } Q_{Cj}(V_R) = \int_0^{V_R} C_j(V) dV$$

## 1.1 Characteristics (curves)

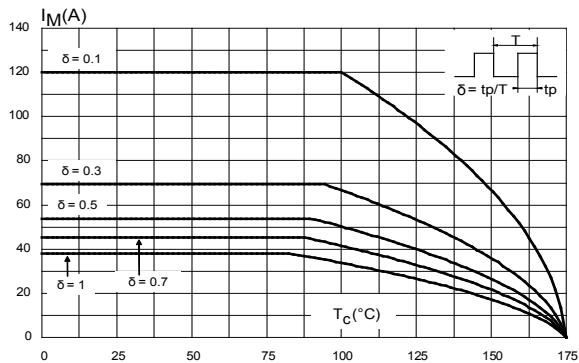
**Figure 1. Forward voltage drop versus forward current (typical values)**



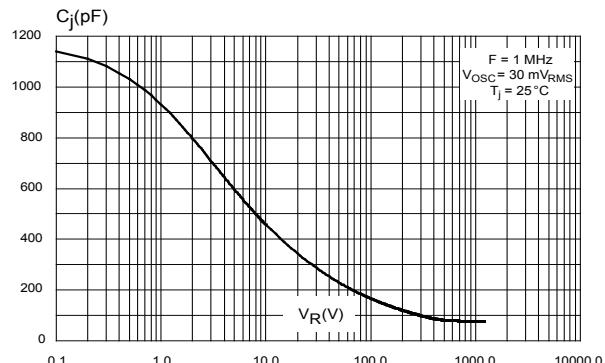
**Figure 2. Reverse leakage current versus reverse voltage applied (typical values)**



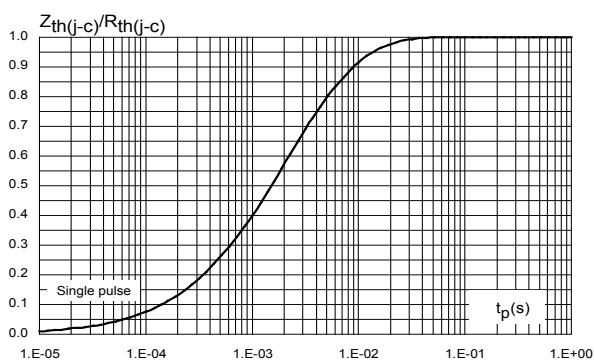
**Figure 3. Peak forward current versus case temperature**



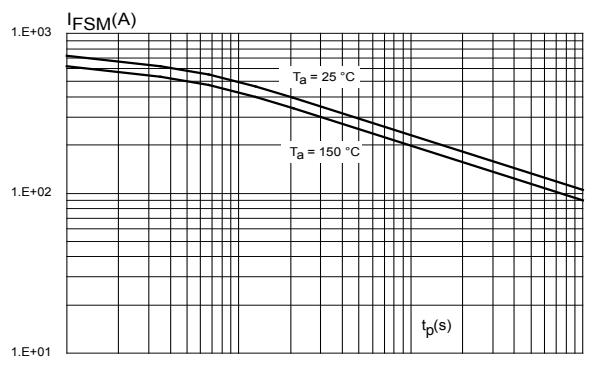
**Figure 4. Junction capacitance versus reverse voltage applied (typical values)**



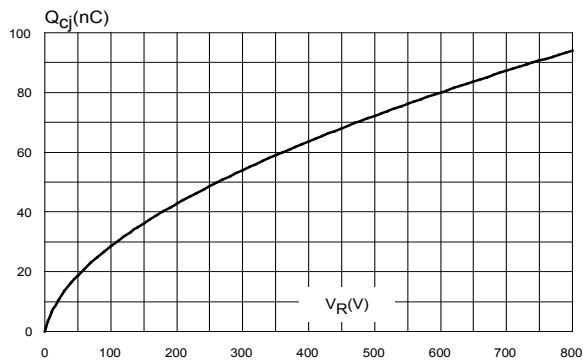
**Figure 5. Relative variation of thermal impedance junction to case versus pulse duration**



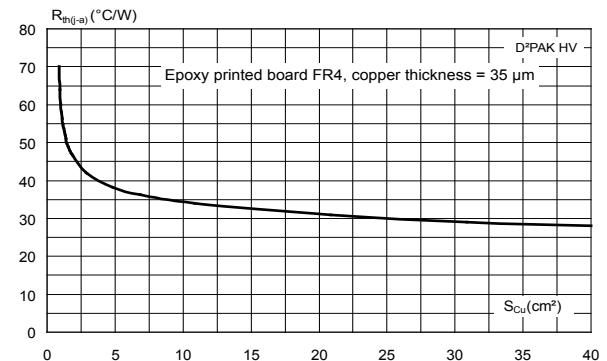
**Figure 6. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)**



**Figure 7. Total capacitive charges versus reverse voltage applied (typical values)**



**Figure 8. Thermal resistance junction to ambient versus copper surface under tab for D<sup>2</sup>PAK package (typical values)**



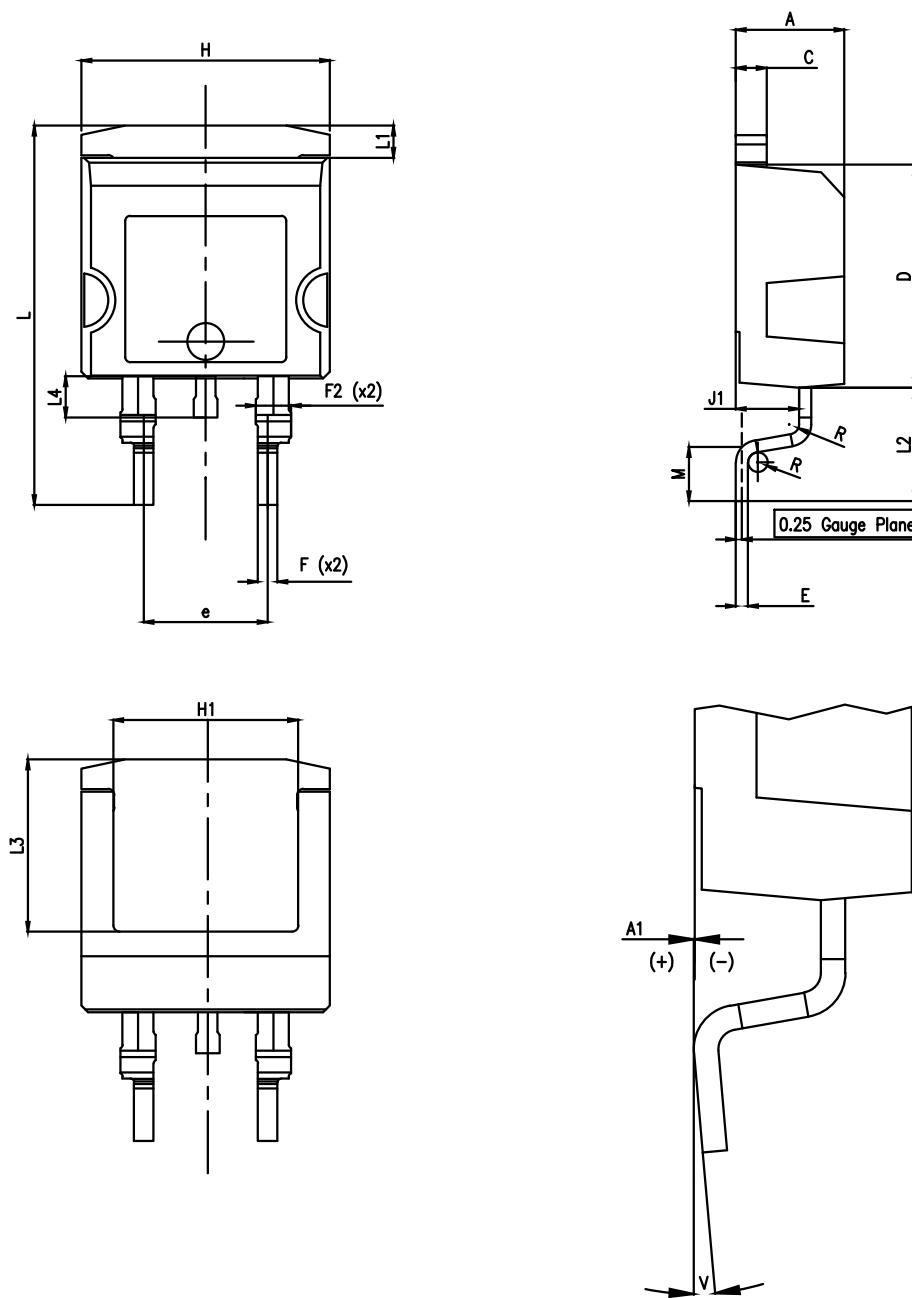
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 2.1 D<sup>2</sup>PAK high voltage package information

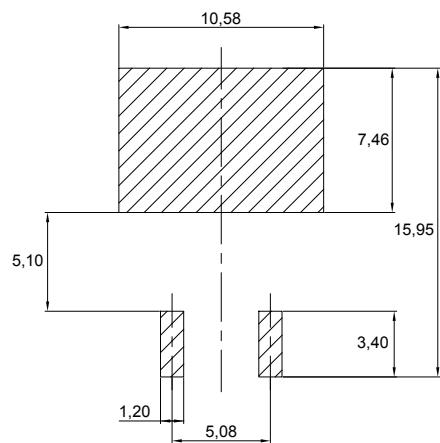
- Epoxy meets UL94, V0

Figure 9. D<sup>2</sup>PAK high voltage package outline



**Table 5.** D<sup>2</sup>PAK high voltage package mechanical data

Ref.	Dimensions		
	Min.	Typ.	Max.
A	4.30	-	4.70
A1	0.03	-	0.20
C	1.17	-	1.37
D	8.95	-	9.35
e	4.98	-	5.18
E	0.50	-	0.90
F	0.78	-	0.85
F2	1.14	-	1.70
H	10.00	-	10.40
H1	7.40	-	7.80
J1	2.49	-	2.69
L	15.30	-	15.80
L1	1.27	-	1.40
L2	4.93	-	5.23
L3	6.85	-	7.25
L4	1.5	-	1.7
M	2.6	-	2.9
R	0.20	-	0.60
V	0°	-	8°

**Figure 10.** D<sup>2</sup>PAK high voltage footprint in mm

## 2.1.1 Creepage distance between Anode and Cathode

Table 6. Creepage distance between anode and cathode

Symbol	Parameter	Value	Unit
Cd <sub>A-K1</sub>	Minimum creepage distance between A and K1 (with top coating)	5.38	mm
Cd <sub>A-K2</sub>	Minimum creepage distance between A and K2 (without top coating)	3.48	mm

Note: D<sup>2</sup>PAK HV creepage distance (anode to cathode) = 5.38 mm min. (refer to IEC 60664-1)

Figure 11. Creepage with top coating

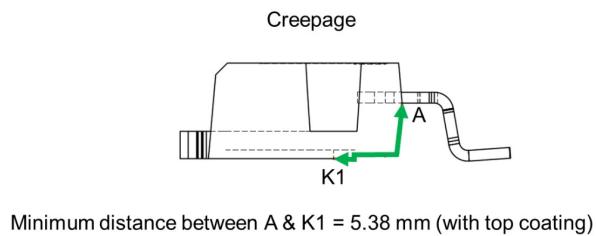
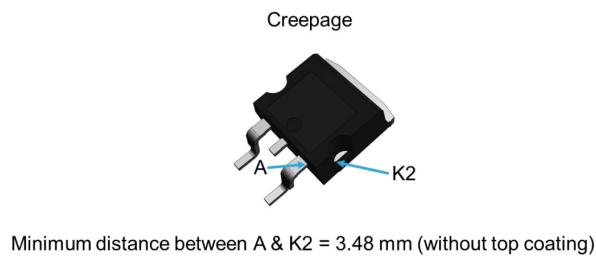


Figure 12. Creepage without top coating



### 3 Ordering information

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**Table 7. Ordering information**

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC15H12G2-TR	SC15H12G2	D <sup>2</sup> PAK HV	1.48 g	1000	Tape and reel

## Revision history

**Table 8. Document revision history**

Date	Revision	Changes
31-Aug-2020	1	First issue.

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